

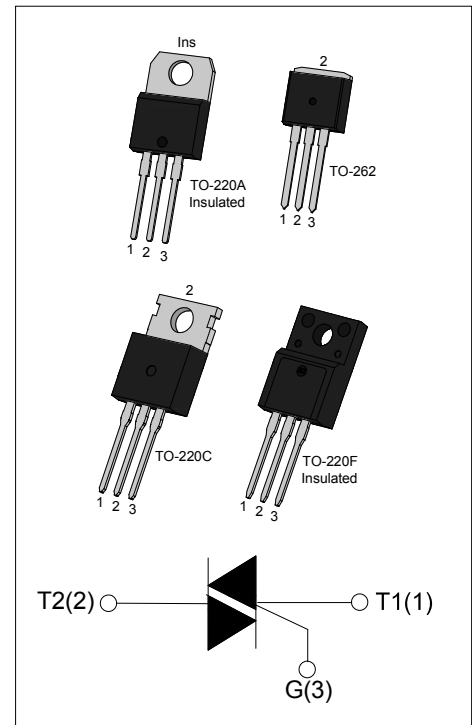


JST139 Series 16A TRIACs

Rev.8.0

DESCRIPTION:

JST139 series triacs with low holding and latching current are especially recommended for use on middle and small resistance type power load. JST139F provides insulation voltage rated at 2000V RMS and JST139A provides insulation voltage rated at 2500V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906). All the packages listed are RoHS compliant. (2011/65/EU)



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM} / V_{RRM}	600/800	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-125	°C
Repetitive peak off-state voltage($T_j=25^\circ\text{C}$)	V_{DRM}	600/800	V
Repetitive peak reverse voltage($T_j=25^\circ\text{C}$)	V_{RRM}	600/800	V
RMS on-state current	TO-220C($T_c=100^\circ\text{C}$)	16	A
	TO-220F(Ins) ($T_c=85^\circ\text{C}$)		
	TO-262 ($T_c=75^\circ\text{C}$)		
	TO-220A(Ins) ($T_c=87^\circ\text{C}$)		
Non repetitive surge peak on-state current ($t_p=20\text{ms}$)	I_{TSM}	140	A
I^2t value for fusing ($t_p=10\text{ms}$)	I^2t	98	A^2s

Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	I - II - III	dI/dt	50	A/ μ s
	IV		10	
Peak gate current		I_{GM}	2	A
Average gate power dissipation		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				D	E	F	B	
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II - III	MAX	5	10	25	50	mA
		IV		10	25	70	70	
V_{GT}		ALL	MAX	1.3				V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN	0.2				V
I_L	$I_G=1.2I_{GT}$	I - III	MAX	15	30	50	80	mA
		II - IV		20	40	100	120	
I_H	$I_T=100\text{mA}$		MAX	10	25	40	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	20	50	100	500	V/ μ s

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=20\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.6	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	1	mA

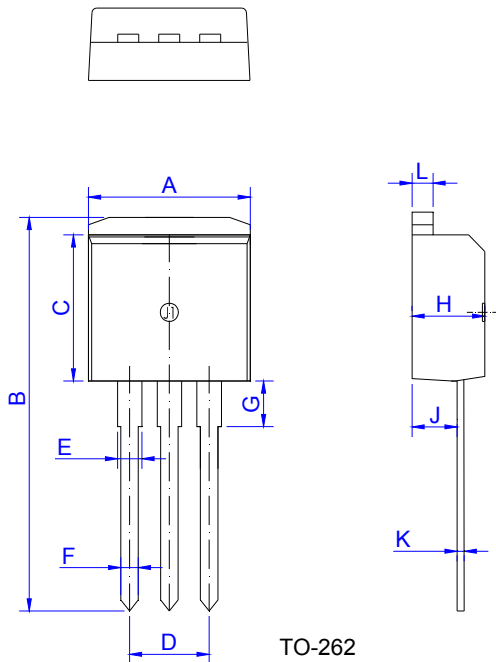
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220C	1.2
		TO-220F(Ins)	2.3
		TO-262	2.7
		TO-220A(Ins)	2.1
			°C/W

ORDERING INFORMATION

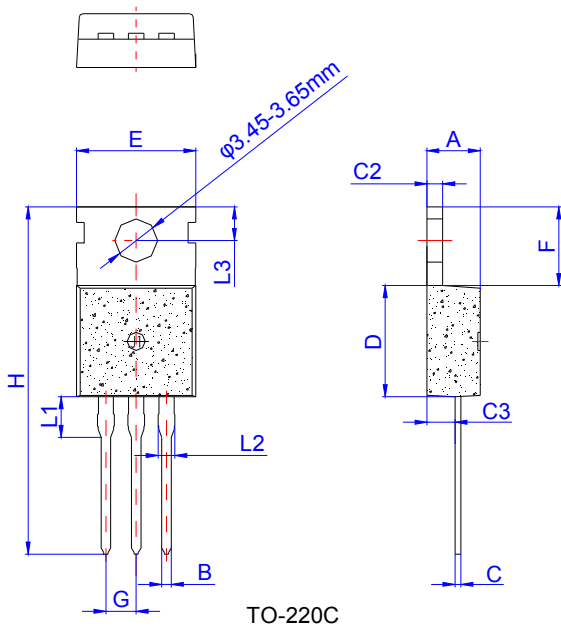
JieJie Microelectronics Co.,Ltd	J	ST	139	F	-600	B
	TRIACs		$I_{T(RMS)}:16A$	600: $V_{DRM}/V_{RRM} \geq 600V$ 800: $V_{DRM}/V_{RRM} \geq 800V$		D: $I_{GT1-3} \leq 5mA$ $I_{GT4} \leq 10mA$ E: $I_{GT1-3} \leq 10mA$ $I_{GT4} \leq 25mA$ F: $I_{GT1-3} \leq 25mA$ $I_{GT4} \leq 70mA$ B: $I_{GT1-3} \leq 50mA$ $I_{GT4} \leq 70mA$
				F:TO-220F(Ins) D:TO-262 C:TO-220C A:TO-220A(Ins)		

PACKAGE MECHANICAL DATA

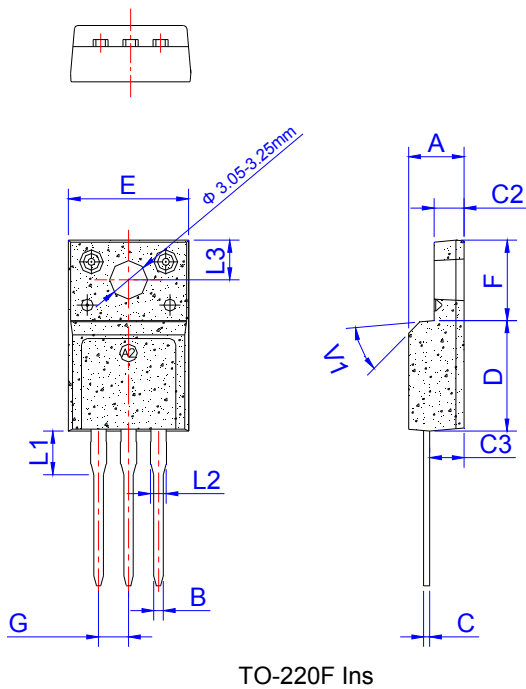


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.95		10.20	0.392		0.402
B	23.85		24.05	0.939		0.947
C	9.40		9.60	0.370		0.378
D	5.00		5.20	0.197		0.205
E	1.35		1.40	0.053		0.055
F	0.80		0.85	0.031		0.033
G	2.70		3.40	0.106		0.134
H	4.45		4.55	0.175		0.179
J	2.30		2.50	0.091		0.098
K	0.48		0.52	0.019		0.020
L	1.30		1.35	0.051		0.053

PACKAGE MECHANICAL DATA

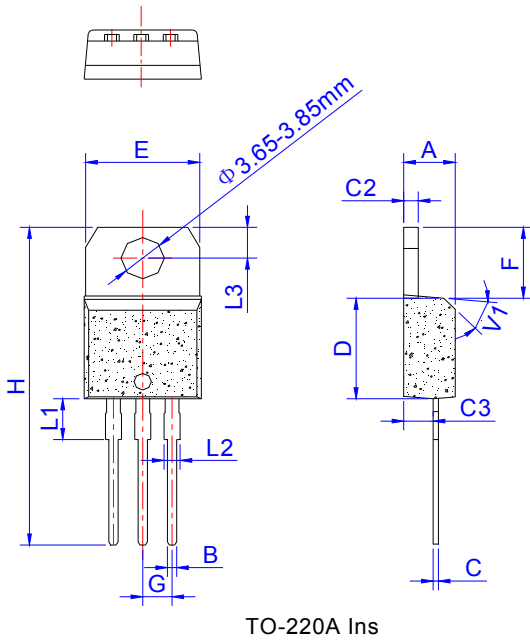


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

FIG.1 Maximum power dissipation versus RMS on-state current

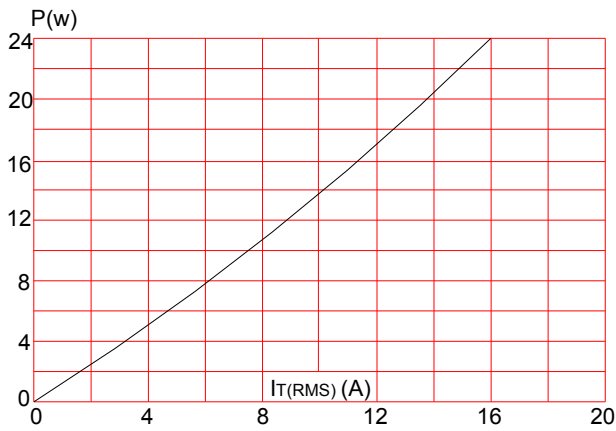


FIG.2: RMS on-state current versus case temperature

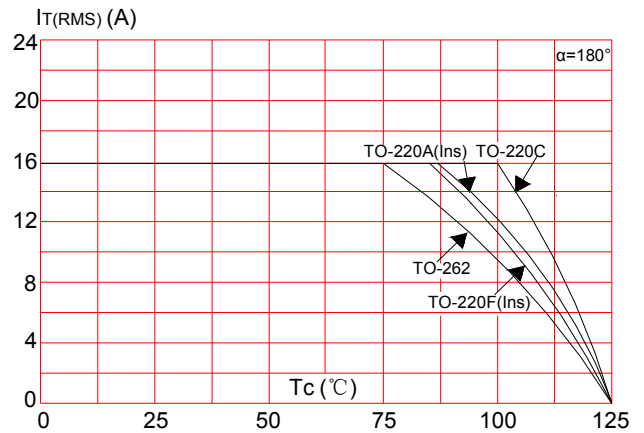


FIG.3: Surge peak on-state current versus number of cycles

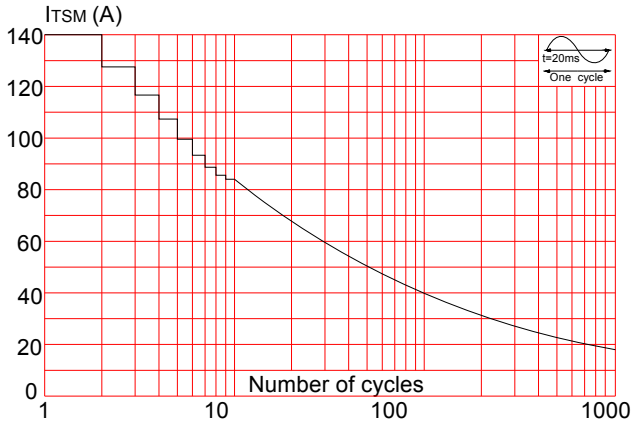


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t (I - II -III: $di/dt < 50\text{A}/\mu\text{s}$; IV: $di/dt < 10\text{A}/\mu\text{s}$)

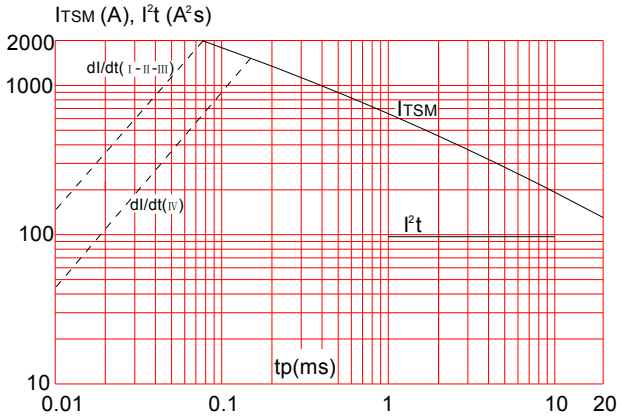


FIG.7: Relative variations of holding current versus junction temperature

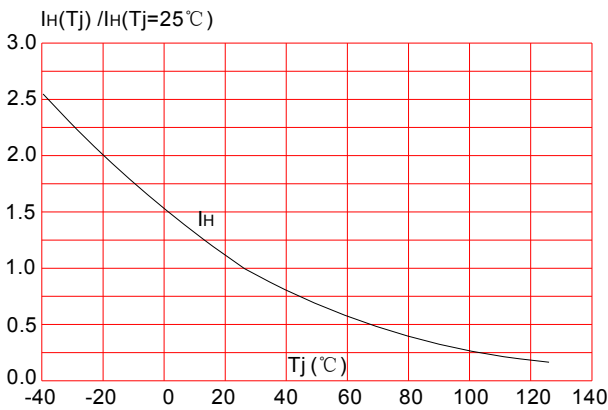


FIG.4: On-state characteristics (maximum values)

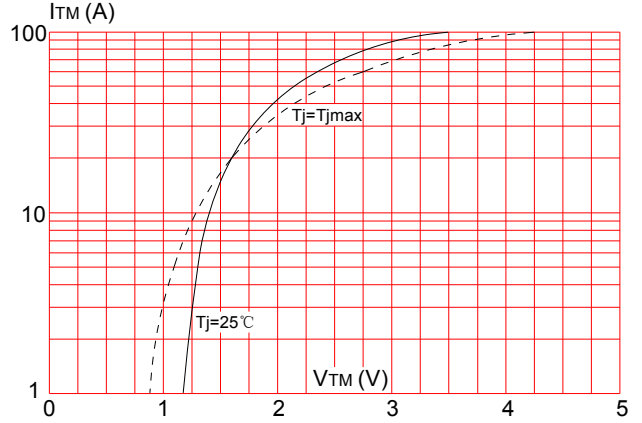


FIG.6: Relative variations of gate trigger current versus junction temperature

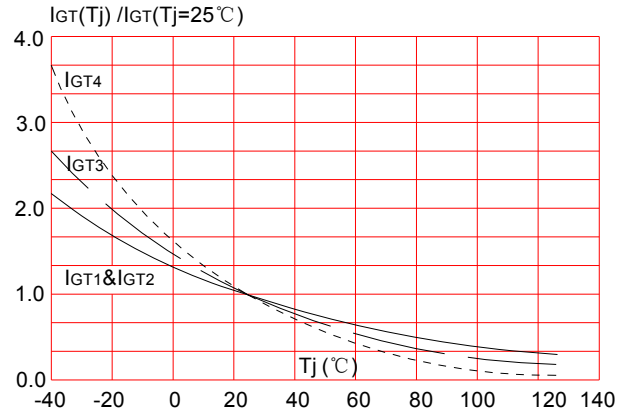
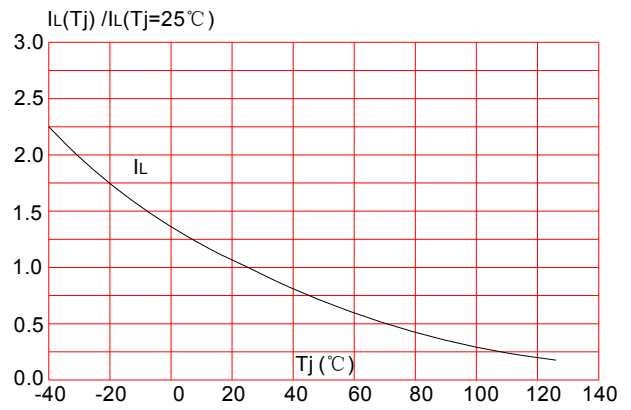


FIG.8: Relative variations of latching current versus junction temperature




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